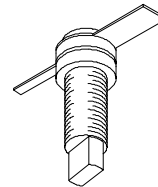


RF & MICROWAVE TRANSISTORS GENERAL PURPOSE AMPLIFIER APPLICATIONS

- EMITTER BALLASTED
- VSWR CAPABILITY $\infty:1$ @ RATED CONDITIONS
- HERMETIC STRIPAC[®] PACKAGE
- $P_{OUT} = 10$ W MIN. WITH 10 dB GAIN @ 1 GHz



.230 2L STUD (S016)

hermetically sealed

ORDER CODE

MSC81010

BRANDING

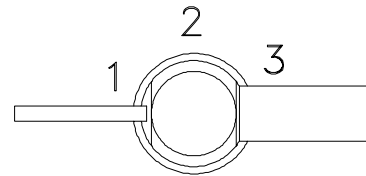
81010

DESCRIPTION

The MSC81010 is a common base hermetically sealed silicon NPN microwave transistor utilizing a fishbone, emitter ballasted geometry with a refractory/gold metallization system. This device is capable of withstanding infinite load VSWR at any phase angle under rated conditions.

The MSC81010 is designed for Class C amplifier applications in the 0.4 - 1.2 GHz frequency range.

PIN CONNECTION



1. Collector

2. Base

3. Emitter

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
P_{DISS}	Power Dissipation*	29	W
I_C	Device Current*	1.0	A
V_{CC}	Collector-Supply Voltage*	35	V
T_J	Junction Temperature	200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	- 65 to +200	$^{\circ}\text{C}$

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance*	6.0	$^{\circ}\text{C/W}$
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*Applies only to rated RF amplifier operation

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

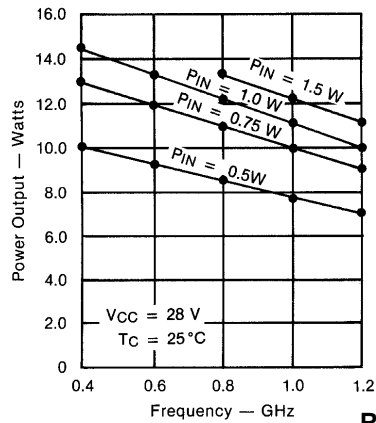
Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV _{CBO}	I _C = 1mA	I _E = 0mA	45	—	—	V
BV _{EBO}	I _E = 1mA	I _C = 0mA	3.5	—	—	V
BV _{CER}	I _C = 10mA	R _{BE} = 10Ω	45	—	—	V
I _{CBO}	V _{CB} = 28V		—	—	2.5	mA
h _{FE}	V _{CE} = 5V	I _C = 500mA	15	—	120	—

DYNAMIC

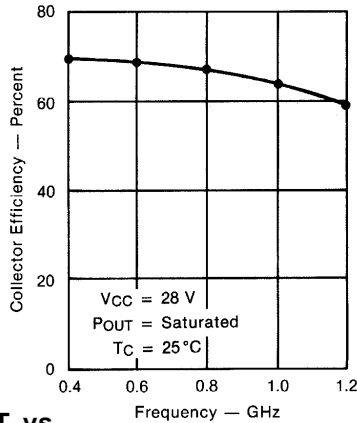
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P _{OUT}	f = 1.0 GHz	P _{IN} = 1.0 W	V _{CC} = 28 V	10	11	—	W
η _c	f = 1.0 GHz	P _{IN} = 1.0 W	V _{CC} = 28 V	60	64	—	%
G _P	f = 1.0 GHz	P _{IN} = 1.0 W	V _{CC} = 28 V	10	10.4	—	dB
C _{OB}	f = 1 MHz	V _{CB} = 28 V		—	—	10	pF

TYPICAL PERFORMANCE

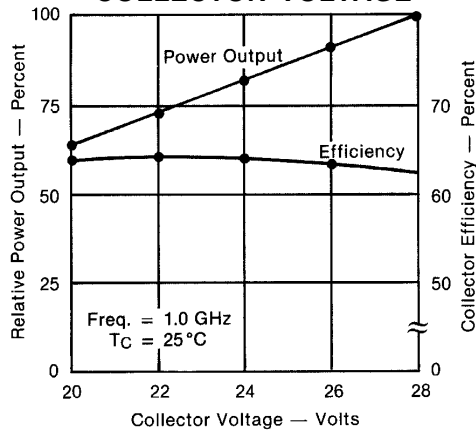
POWER OUTPUT vs FREQUENCY



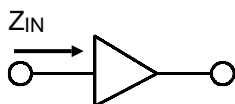
FREQUENCY vs COLLECTOR EFFICIENCY



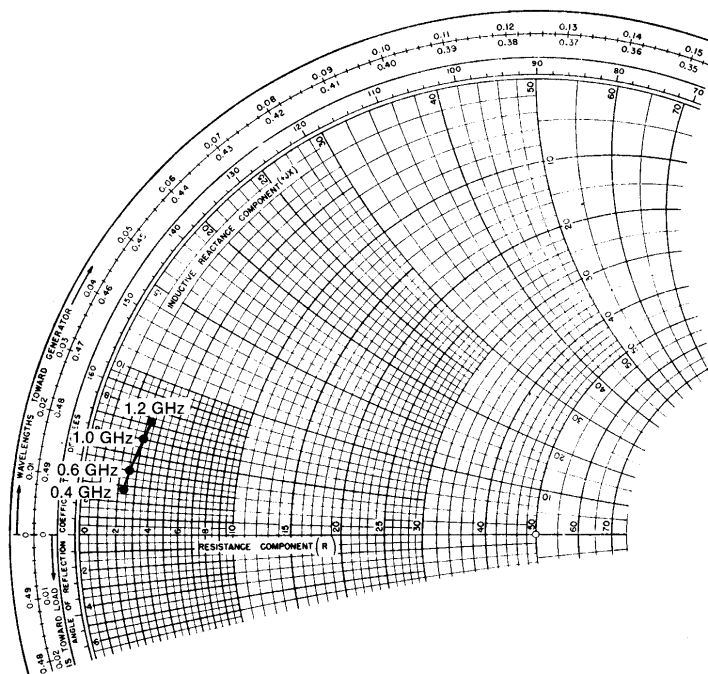
RELATIVE POWER OUTPUT vs COLLECTOR VOLTAGE



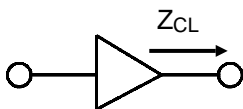
IMPEDANCE DATA

TYPICAL INPUT
IMPEDANCE

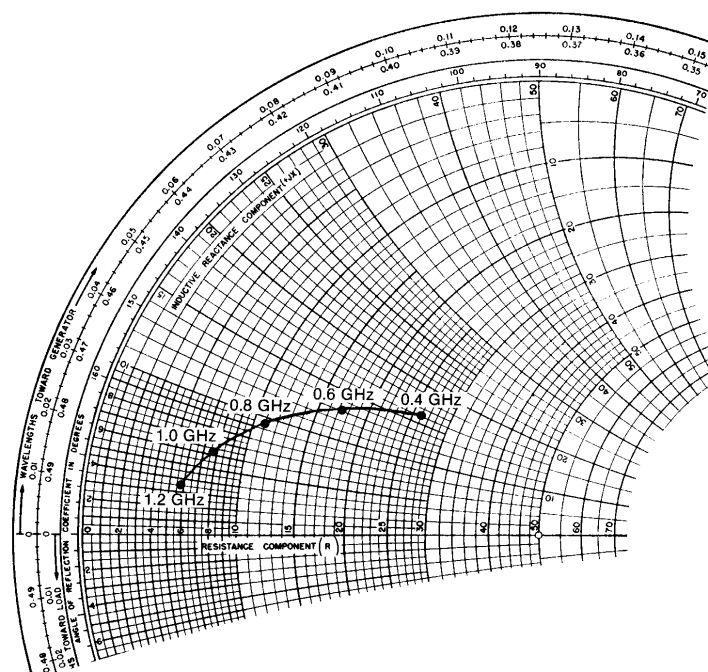
$P_{IN} = 1.0 \text{ W}$
 $V_{CC} = 28 \text{ V}$
 Normalized to 50 ohms



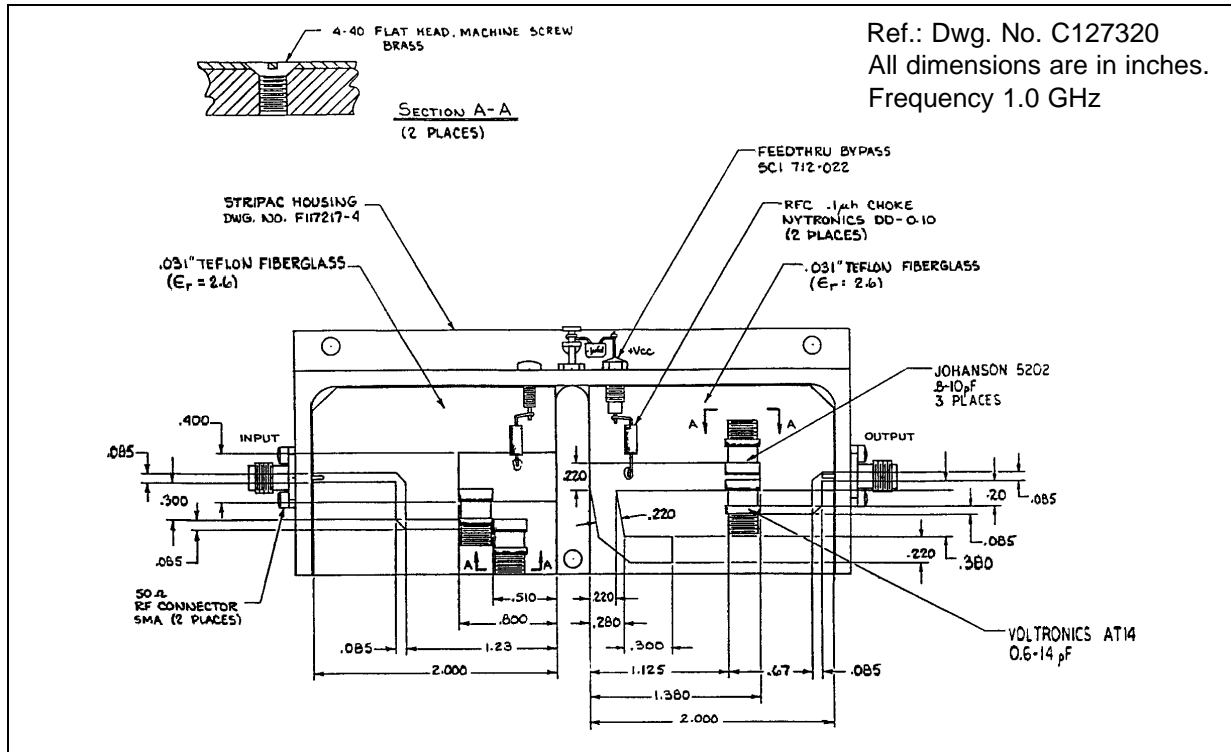
FREQ.	$Z_{IN} (\Omega)$	$Z_{CL} (\Omega)$
0.4 GHz	$2.3 + j 2.7$	$26.0 + j 16.0$
0.6 GHz	$2.5 + j 4.0$	$17.2 + j 13.0$
0.8 GHz	$2.8 + j 5.0$	$11.0 + j 9.5$
1.0 GHz	$3.0 + j 6.0$	$7.7 + j 6.3$
1.2 GHz	$3.3 + j 7.2$	$5.8 + j 3.5$

TYPICAL COLLECTOR
LOAD IMPEDANCE

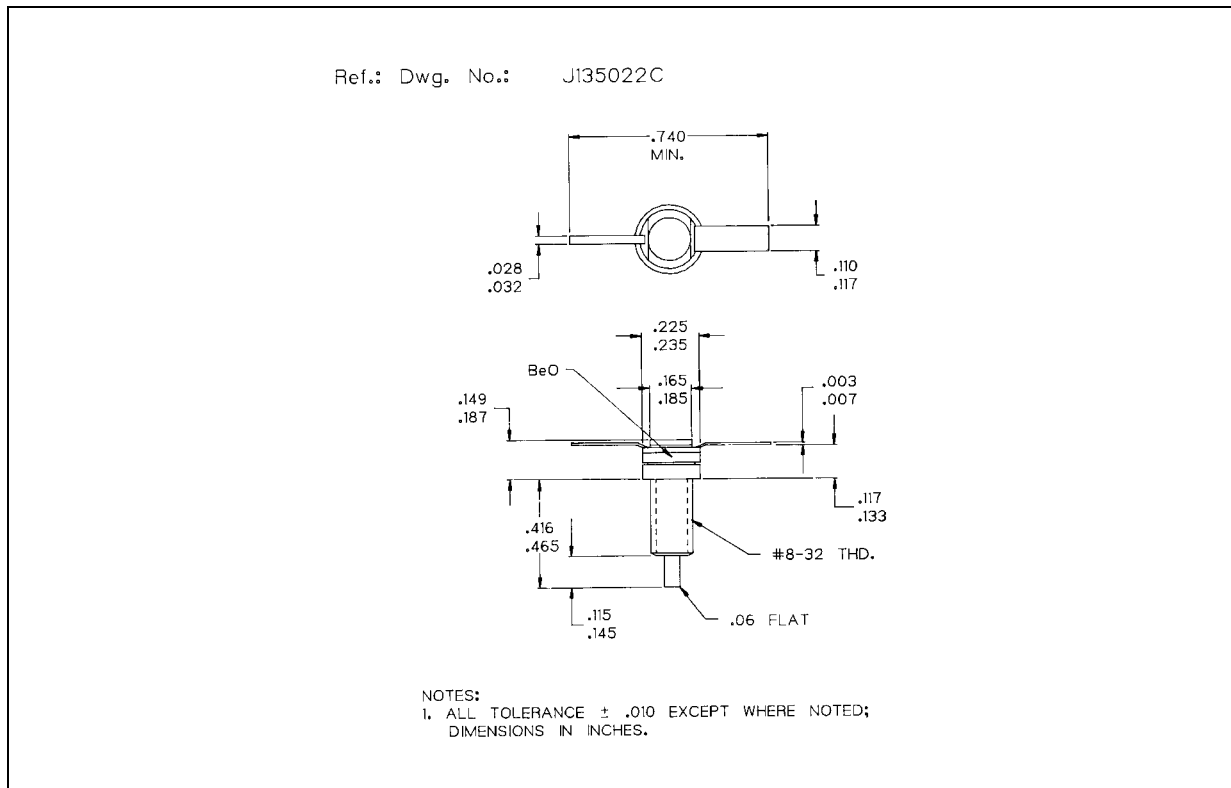
$P_{OUT} = \text{Saturated}$
 $V_{CC} = 28 \text{ V}$
 Normalized to 50 ohms



TEST CIRCUIT



PACKAGE MECHANICAL DATA



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